

General Description

The AGM412S combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

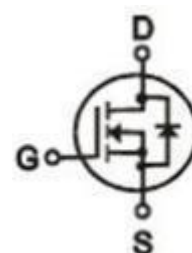
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDS(ON)	ID
40V	11mΩ	13A

SOP-8 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM412S	AGM412S	SOP8	330mm	12mm	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	40	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(TA=25°C) (Note 1)	13	A
	Drain Current-Continuous(TA=100°C)	8.5	A
IDM (pulse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	52	A
PD	Maximum Power Dissipation(TA=25°C)	2.5	w
	Maximum Power Dissipation(TA=100°C)	1.0	w
EAS	Avalanche energy (Note 3)	90	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	50	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	40	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=40V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	1.4	2.2	V
gFS	Forward Transconductance	VDS=5V,ID=5A	--	10	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=8A	--	11	14	mΩ
		VGS=4.5V, ID=5A	--	13.5	22	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VGS=0V, VDS=20V,F=1MHZ	--	1125	--	pF
Coss	Output Capacitance		--	103	--	pF
Crss	Reverse Transfer Capacitance		--	77	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=20V, ID=8A,RL=1Ω,RGEN=3Ω	--	9	--	nS
tr	Turn-on Rise Time		--	8	--	nS
td(off)	Turn-Off Delay Time		--	29	--	nS
tf	Turn-Off Fall Time		--	14	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=20V, ID=8A	--	18	--	nC
Qgs	Gate-Source Charge		--	3.2	--	nC
Qgd	Gate-Drain Charge		--	3.8	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	13	A
VSD	Forward on Voltage	VGS=0V,IS=8A	--	--	1.2	V
trr	Reverse Recovery Time	IF=8A , dI/dt=100A/μs , TJ=25℃	--	20	--	ns
Qrr	Reverse Recovery Charge		--	10	--	nc

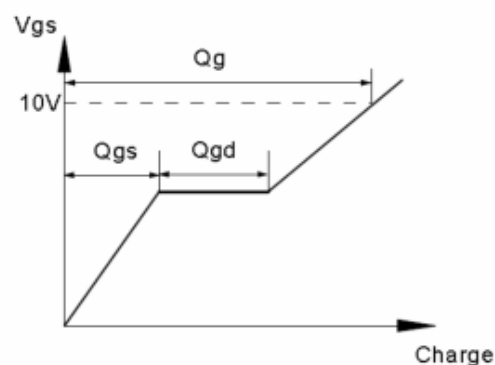
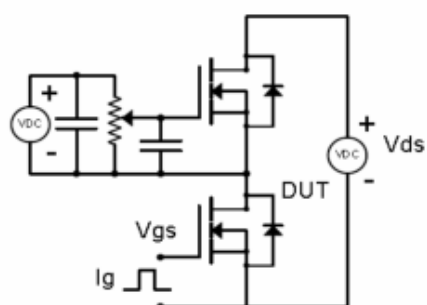
Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

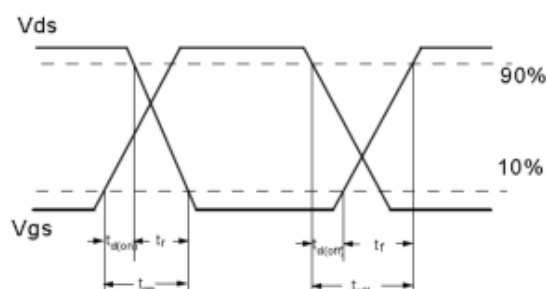
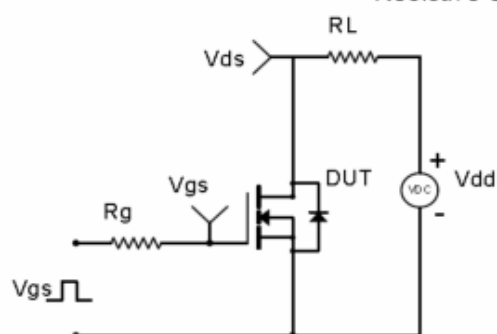
Notes 3.EAS condition: TJ=25°C, VDD=25V, Vgs=10V, ID=19A, L=0.5mH, RG=25ohm

Test Circuit & Waveform

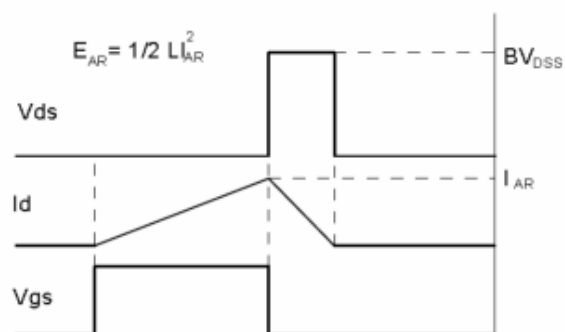
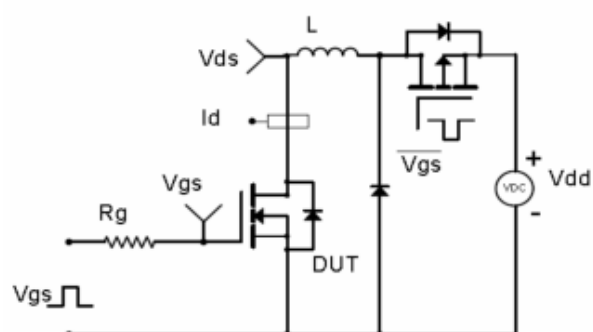
Gate Charge Test Circuit & Waveform



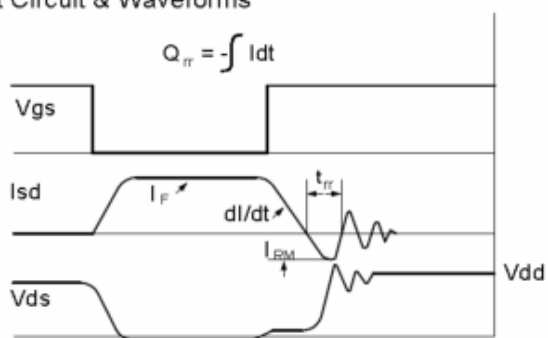
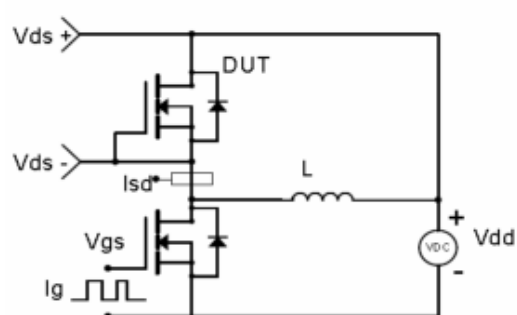
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Typical Performance Characteristics

Fig.1 Output Characteristics

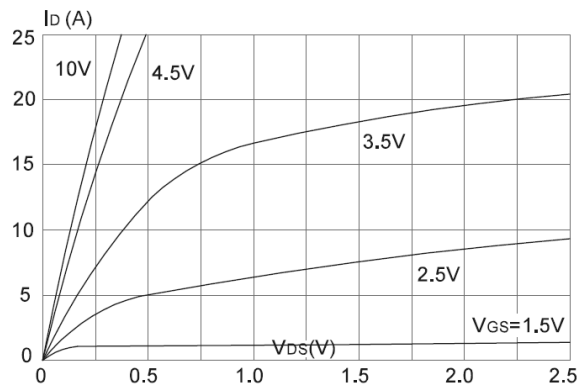


Fig.2 Typical Transfer Characteristics

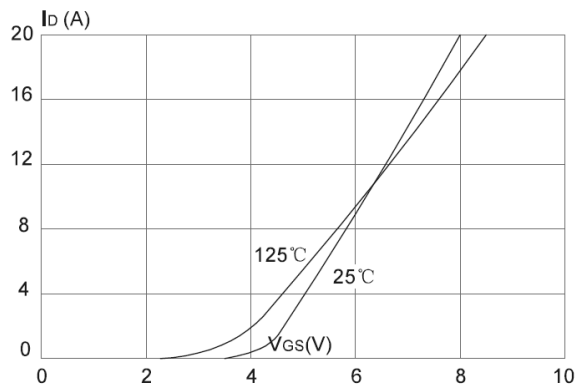


Fig.3 On-resistance VS Drain Current

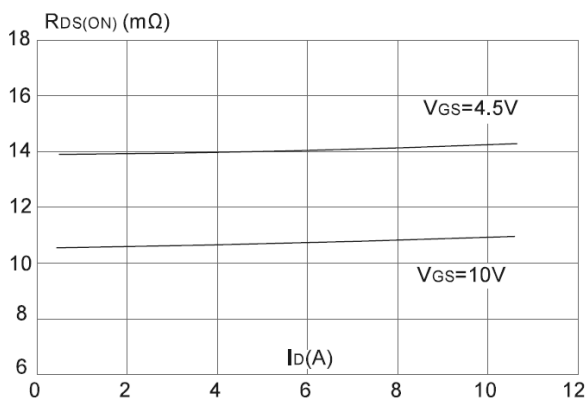


Fig. 4 Body Diode Characteristics

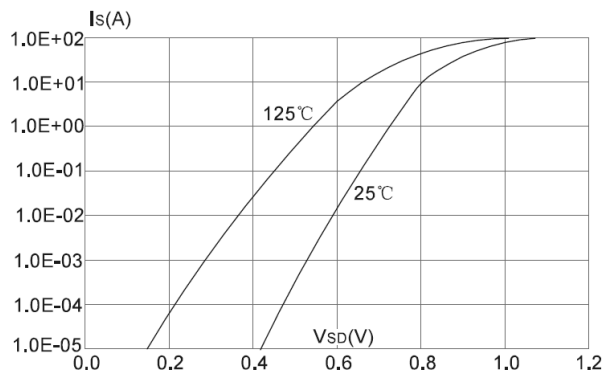


Fig.5 Gate Charge Characteristics

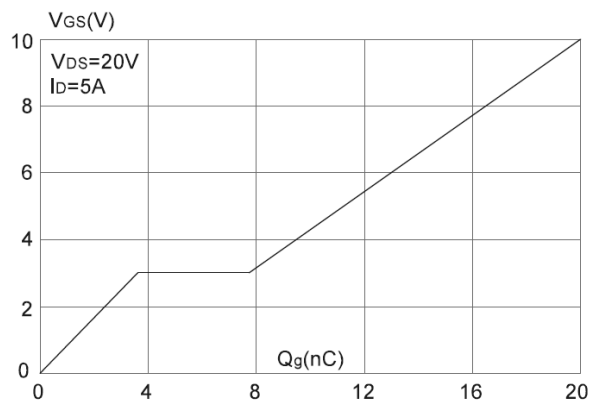


Fig. 6 Capacitance Characteristics

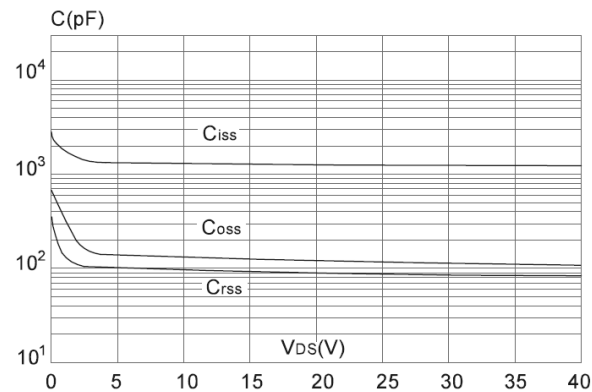


Fig.7 Normalized Breakdown Voltage
VS Junction Temperature

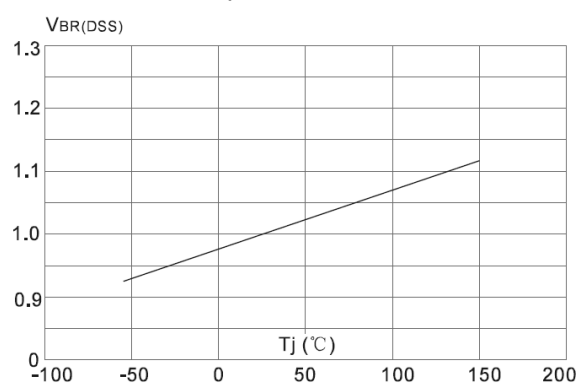


Fig. 8 Normalized On-Resistance Variation VS
Junction Temperature

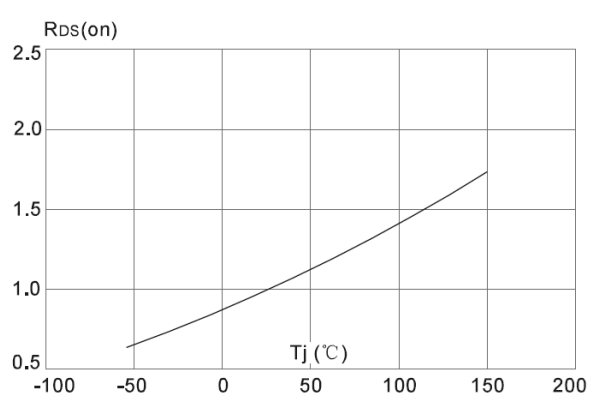


Fig.9 Maximum Continuous Drain Current VS.
Ambient Temperature

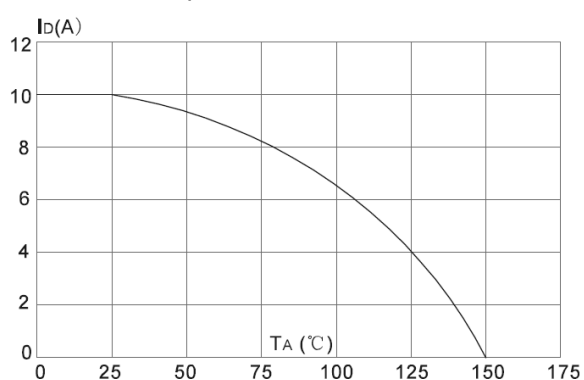


Fig.10 Safe Operating Area

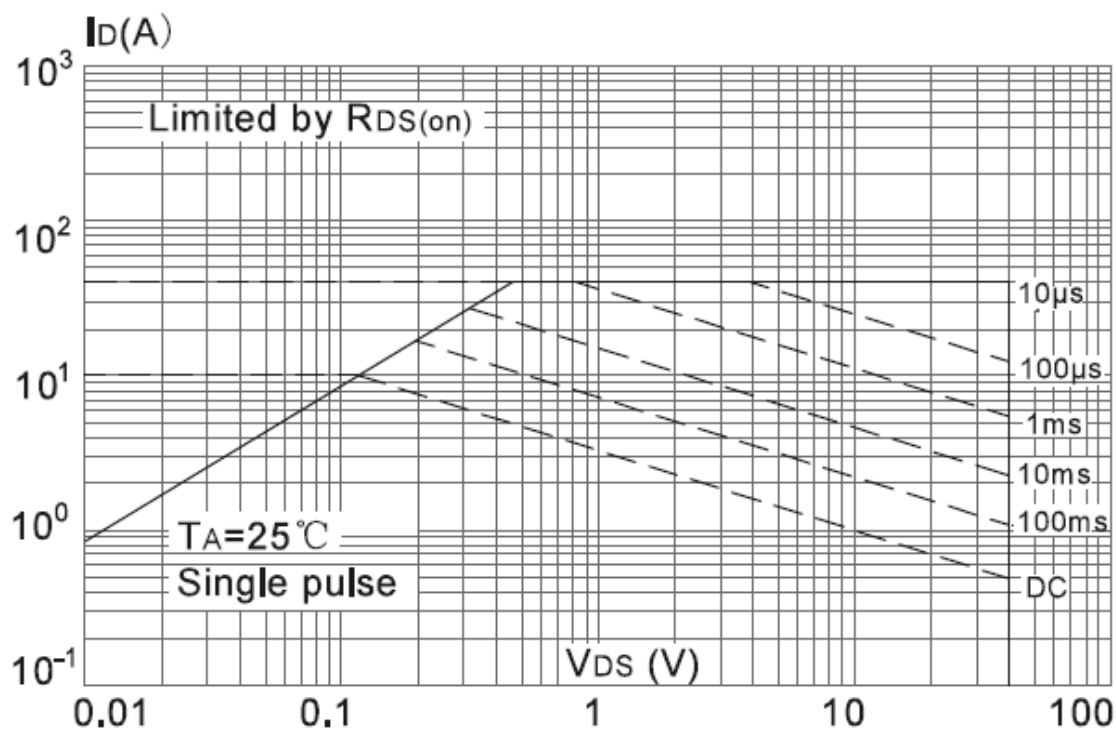
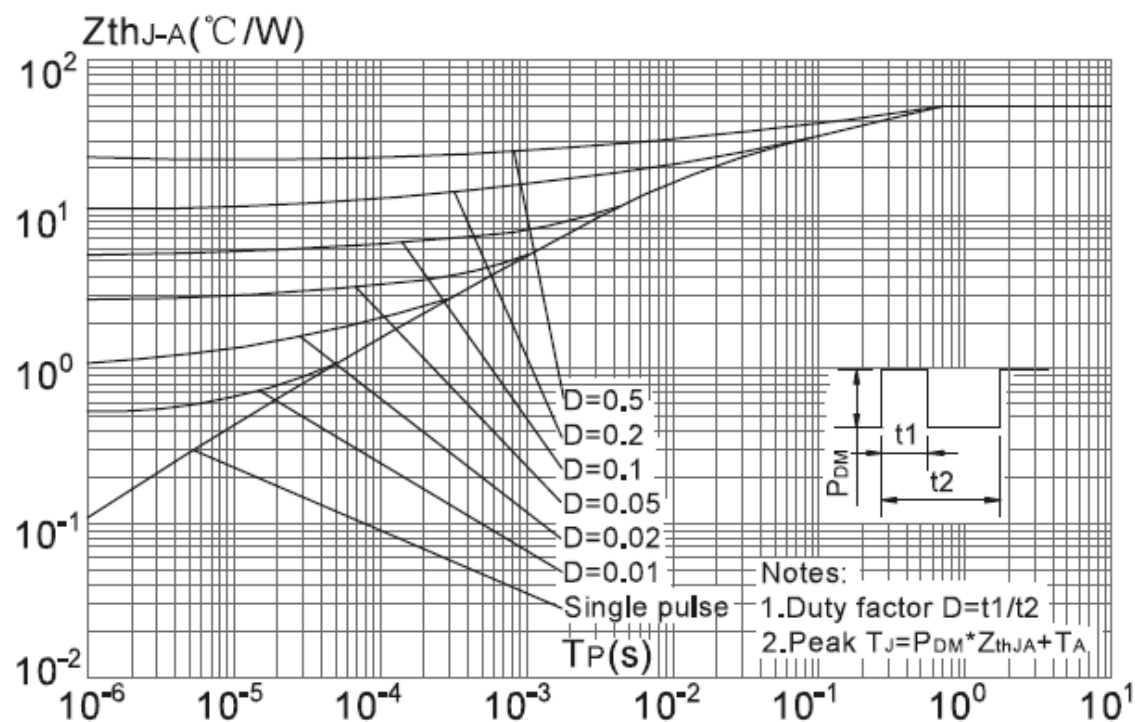
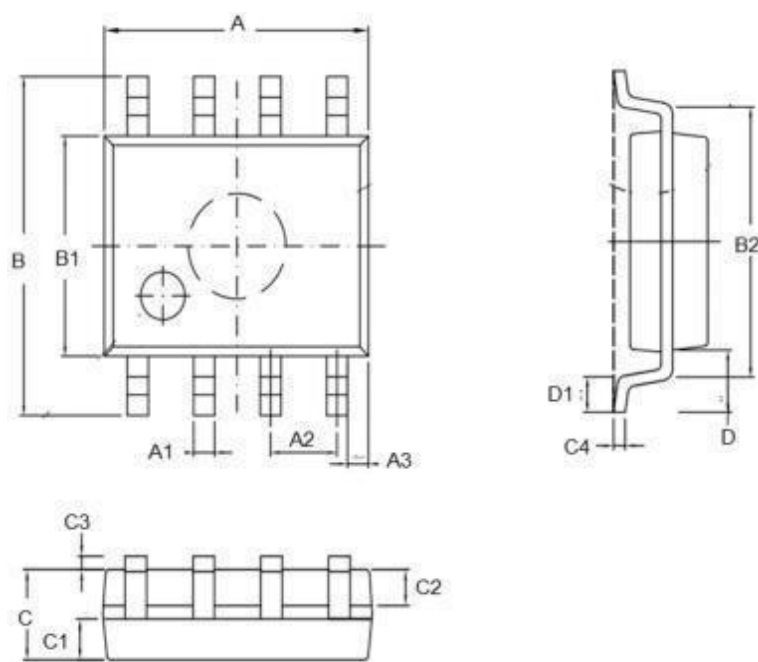


Fig. 11 Transient Thermal Response Curve



•Dimensions(SOP8)

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.00	C	1.30		1.50
A1	0.37		0.47	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.19	0.20	0.23
B1	3.80		4.00	D		1.05	
B2		5.00		D1	0.40		0.62



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